

# Adjustable Voltage Reference – TL431

### Precision programmable Shunt Voltage Reference in bare die form

## Description

The TL431 three-terminal shunt reference combines low temperature co-efficient zener band-gap regulation with programmability. The device operates over a wide 1mA to 100mA current range with voltage adjustable from  $V_{REF}$  (2.5V) to 36V, set via x2 external resistors. With high temperature stability and typical dynamic impedance of 0.27 $\Omega$ , these references make excellent replacements for zener diodes in many high reliability applications. By default, the 2.5V V<sub>REF</sub> provides a stable reference from 5V logic supplies. The device is simple to implement, highly reliable and can be used as either positive or negative reference.

## Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection (Space)
  + MIL-PRF-38534 Class K\_AT

#### LAT = Lot Acceptance Test.

For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

## Supply Formats:

- Defact Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 280µm(11 Mils) On request
- In Metal or Ceramic package On request

### Features:

- Programmable output voltage to 36
- ±0.5% reference voltage tolerance a 25°C
- Low dynamic output impedance 0.27Ω Typ
- Sink current capability: mA to 100 mA
- Band-gap reference corrects temperature drift
- Full military temperature range
- Smaller div size than industry peers

## Die Dimensions in µm (mils)



## **Mechanical Specification**

Die Size (Unsawn)	760 x 600 30 x 24	µm mils	
Minimum Bond Pad Size	92 x 92 3.62 x 3.62	µm mils	
Die Thickness	280 (±20) 11 (±0.8)	µm mils	
Top Metal Composition	Al 1%Si 1.4µm		
Back Metal Composition	N/A – Bare Si		



**Rev 1.0** 

02/05/20



#### **Rev 1.0** 02/05/20 Pad Layout and Functions COCRDINATES PAD FUNCTION <u>v (</u>) 3 1 2 Υ 1 CATHODE 442 600µm (23.62 mils) 2 325 437 ANO REFERENCE 525 3 450 CONNECT CHIP BACK TO ANODE 0,0 760µm (29.92 mils) Symbol & functional block diagram CATHODE (1) RENCE (3) CATHODE (1) + $\bigcirc$ **REFERENCE** (3 О 2.5V REF ANODE (2) ANODE (2)





### Rev 1.0 02/05/20

## Absolute Maximum Ratings<sup>1</sup> $T_A = 25^{\circ}C$ unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIZ
Cathode to Anode Voltage	node Voltage V <sub>KA</sub> 40		V.
Cathode Current Range, Continuous	Ι <sub>κ</sub>	-100 to +150	n.A
Reference Input Current Range, Continuous	I <sub>REF</sub>	-0.05 to 10	hA
Operating Junction Temperature Range	TJ	150	0°
Storage Temperature	T <sub>STG</sub>	-65 to 150	°C

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.

### **Recommended Operating Conditions**

PARAMETER	SYMBOL	MN	MAX	UNIT
Cathode Voltage	V <sub>KA</sub>	0.96	36	V
Cathode Current	Ι <sub>κ</sub>	0.5	100	mA
Ambient Operating Temperature Range	T <sub>A</sub>	-55 to	o 125	°C

## Electrical Characteristics, T<sub>A</sub> = 25°C, V<sub>KA</sub> = V<sub>REF</sub> = 10mA unless otherwise stated

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Reference input voltage	V <sub>REF</sub>	V <sub>KA</sub> = V <sub>RE5, 4K</sub> = 10mA	2.483	2.495	2.507	V
Reference input voltage, Deviation over temperature range	$\Delta V_{REF}$	V <sub>RL</sub> <del>7</del> V <sub>BEF</sub> , I <sub>K</sub> = 10mA, -55℃ ≤ T <sub>A</sub> ≤ +125°C	-	14	34	mV
Ratio of change in		$I_{\rm K}$ = 10mA , $\Delta V_{\rm KA}$ = 10V to $V_{\rm REF}$	-0.4	-	-2.7	
reference input voltage to change in cathode to anode voltage	reference input voltage to change in cathode to anode voltage $\Delta V_{REF}$	$I_{\rm K}$ = 10mA , $\Delta V_{\rm KA}$ = 36V to 10V	-0.4	-	-2.0	mV/V
Reference input current	I <sub>REF</sub>	I <sub>K</sub> = 10mA, R1 = 10kΩ, R2 = ∞	-	1.8	4	
		I <sub>K</sub> = 10mA, R1 = 10kΩ, R2 = ∞, -55°C ≤ T <sub>A</sub> ≤ +125°C	-	-	6.5	μA
Reference input current, Deviator over temperature range	$\Delta I_{REF}$	I <sub>K</sub> = 10mA, R1 = 10kΩ, R2 = ∞	-	0.8	2.5	μA
Minimum cathode current for regulation	I <sub>K(MIN)</sub>	$V_{KA} = V_{REF}$		0.25	0.5	mA
Off-State cathode current	I <sub>K(OFF)</sub>	V <sub>KA</sub> = 36V, V <sub>REF</sub> = 0V	-	20	1000	nA
Dynamic impedance	ZKA	$I_{\rm K}$ = 10mA to 100mA , f $\leq$ 1.0KHz	-	0.27	0.5	Ω









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